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(54) MACHINING METHOD OF SILICON SINGLE-CRYSTAL INGOT

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a machining method that can slice a wafer with a high yield without unnecessarily thickening the wafer in slicing from a silicon single-crystal ingot with a large diameter.

SOLUTION: In this machining method for slicing the wafer from a silicon single-crystal ingot, prior to slicing the wafer, the single-crystal ingot is divided and cut in parallel with the axis direction. After that, the wafer with desired thickness is sliced from the divided ingot.

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